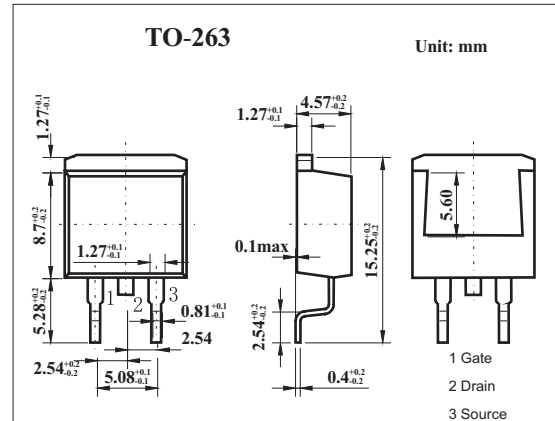


N-Channel Enhancement Mode MOSFET

2SK3269

■ Features

- 4.5 V drive available
- Low on-state resistance
 $R_{DS(on)1} = 12 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 18 \text{ A)}$
- Low gate charge
 $Q_G = 30 \text{ nC TYP. (} I_D = 35 \text{ A, } V_{DD} = 16 \text{ V, } V_{GS} = 10 \text{ V)}$
- Built-in gate protection diode
- Surface mount device available



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DS}	100	V
Gate to source voltage	V_{GS}	± 20	V
Drain current	I_D	± 35	A
	I_{DP}^*	± 140	A
Power dissipation	P_D	$T_a=25^\circ\text{C}$	1.5
		$T_c=25^\circ\text{C}$	40
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain source surrender voltage	V_{DSS}	$I_D=1\text{mA, } V_{GS}=0$	100			V
Drain cut-off current	I_{DSS}	$V_{DS}=20\text{V, } V_{GS}=0$			10	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 20\text{V, } V_{DS}=0$			± 10	μA
Gate cutoff voltage	$V_{GS(off)}$	$V_{DS}=10\text{V, } I_D=1\text{mA}$	1.0		2.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10\text{V, } I_D=12\text{A}$	9.0			S
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V, } I_D=18\text{A}$		8.5	12	$\text{m}\Omega$
		$V_{GS}=4.5\text{V, } I_D=18\text{A}$		12	19	$\text{m}\Omega$
Input capacitance	C_{iss}	$V_{DS}=10\text{V, } V_{GS}=0, f=1\text{MHz}$		1300		pF
Output capacitance	C_{oss}			570		pF
Reverse transfer capacitance	C_{rss}			300		pF
Turn-on delay time	t_{on}	$I_D=18\text{A, } V_{GS(on)}=10\text{V, } R_G=10\Omega, V_{DD}=10\text{V}$		70		ns
Rise time	t_r			1220		ns
Turn-off delay time	t_{off}			100		ns
Fall time	t_f			180		ns